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EFFICIENT POWER CONVERSION

Development Board / Demonstration Board Notification

The EPC9006 board is intended for product evaluation purposes only and is not intended for commercial use. As an evaluation tool, it is not designed for compliance with the European Union directive on electromagnetic compatibility or any other such directives or regulations.

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Development Board EPC9006 Quick Start Guide

100 V Half-Bridge with Gate Drive, Using EPC2007

EFFICIENT POWER CONVERSION

DESCRIPTION

The EPC9006 development board is a 100 V maximum device voltage, 5 A maximum output current, half bridge with onboard gate drives, featuring the EPC2007 enhancement mode (eGaN®) field effect transistor (FET). The purpose of this development board is to simplify the evaluation process of the EPC2007 eGaN FET by including all the critical components on a single board that can be easily connected into any existing converter.

The EPC9006 development board is 2" x 1.5" and contains not only two EPC2007 eGaN FET in a half bridge configuration using National LM5113 gate driver, supply and bypass capacitors. The board contains all critical components and layout for optimal switching performance. There are also various probe points to facilitate simple waveform measurement and efficiency calculation. A complete block diagram of the circuit is given in Figure 1.

For more information on the EPC2007s eGaN FET please refer to the datasheet available from EPC at www.epc-co.com. The datasheet should be read in conjunction with this quick start guide.

Table 1 Performance Summary (T_A = 25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNITS
V_{DD}	Gate Drive Input Supply Range		7	12	V
V_{IN}	Bus Input Voltage Range			70*	V
V_{OUT}	Switch Node Output Voltage			100	V
I_{OUT}	Switch Node Output Current			5*	A
V_{PWM}	PWM Logic Input Voltage Threshold	Input 'High'	3.5	6	V
		Input 'Low'	0	1.5	V
	Minimum 'High' State Input Pulse Width	V_{PWM} rise and fall time < 10ns	30		ns
	Minimum 'Low' State Input Pulse Width	V_{PWM} rise and fall time < 10ns	100#		ns

*Assumes inductive load, maximum current depends on die temperature – actual maximum current with be subject to switching frequency, bus voltage and thermals.
Limited by time needed to 'refresh' high side bootstrap supply voltage.

Quick Start Procedure

Development board EPC9006 is easy to set up to evaluate the performance of the EPC2007 eGaN FET. Refer to Figure 2 for proper connect and measurement setup and follow the procedure below:

1. With power off, connect the input power supply bus to +VIN (J5,J6) and ground / return to –VIN (J7,J8).
2. With power off, connect the switch node of the half bridge OUT (J3,J4) to your circuit as required.
3. With power off, connect the gate drive input to +VDD (J1, Pin-1) and ground return to –VDD (J1, Pin-2).
4. With power off, connect the input PWM control signal to PWM (J2, Pin-1) and ground return to any of the remaining J2 pins.
5. Turn on the gate drive supply – make sure the supply is between 7 V and 12 V range.
6. Turn on the bus voltage to the required value (do not exceed the absolute maximum voltage of 100 V on VOUT).
7. Turn on the controller / PWM input source and probe switching node to see switching operation.
8. Once operational, adjust the bus voltage and load PWM control within the operating range and observe the output switching behavior, efficiency and other parameters.
9. For shutdown, please follow steps in reverse.

NOTE. When measuring the high frequency content switch node (OUT), care must be taken to avoid long ground leads. Measure the switch node (OUT) by placing the oscilloscope probe tip through the large via on the switch node (designed for this purpose) and grounding the probe directly across the GND terminals provided. See Figure 3 for proper scope probe technique. Do not let the probe tip touch the low-side die.

THERMAL CONSIDERATIONS

The EPC9006 development board showcases the EPC2007 eGaN FET. Although the electrical performance surpasses that for traditional Si devices, their relatively smaller size does magnify the thermal management requirements. The EPC9006 is intended for bench evaluation with low ambient temperature and convection cooling. The addition of heat-sinking and forced air cooling can significantly increase the current rating of these devices, but care must be taken to not exceed the absolute maximum die temperature of 125°C.

NOTE. The EPC9006 development board does not have any current or thermal protection on board.

Figure 1: Block Diagram of EPC9006 Development Board

Figure 4: Typical Waveforms for V_{IN} = 48 V to 5 V/5 A (1000kHz) Buck converter
CH1: V_{PWM} Input voltage – CH2: (I_{OUT}) Switch node current – CH4: (V_{OUT}) Switch node voltage

Figure 2: Proper Connection and Measurement Setup

Figure 3: Proper Measurement of Switch Node – OUT

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Development Board EPC9006 Quick Start Guide

100 V Half-Bridge with Gate Drive, Using EPC2007

EFFICIENT POWER CONVERSION

DESCRIPTION

The EPC9006 development board is a 100 V maximum device voltage, 5 A maximum output current, half bridge with onboard gate drives, featuring the EPC2007 enhancement mode (eGaN®) field effect transistor (FET). The purpose of this development board is to simplify the evaluation process of the EPC2007 eGaN FET by including all the critical components on a single board that can be easily connected into any existing converter.

The EPC9006 development board is 2" x 1.5" and contains not only two EPC2007 eGaN FET in a half bridge configuration using National LM5113 gate driver, supply and bypass capacitors. The board contains all critical components and layout for optimal switching performance. There are also various probe points to facilitate simple waveform measurement and efficiency calculation. A complete block diagram of the circuit is given in Figure 1.

For more information on the EPC2007s eGaN FET please refer to the datasheet available from EPC at www.epc-co.com. The datasheet should be read in conjunction with this quick start guide.

Table 1 Performance Summary (T_A = 25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNITS
V_{DD}	Gate Drive Input Supply Range		7	12	V
V_{IN}	Bus Input Voltage Range			70*	V
V_{OUT}	Switch Node Output Voltage			100	V
I_{OUT}	Switch Node Output Current			5*	A
V_{PWM}	PWM Logic Input Voltage Threshold	Input 'High'	3.5	6	V
		Input 'Low'	0	1.5	V
	Minimum 'High' State Input Pulse Width	V_{PWM} rise and fall time < 10ns	30		ns
	Minimum 'Low' State Input Pulse Width	V_{PWM} rise and fall time < 10ns	100#		ns

*Assumes inductive load, maximum current depends on die temperature – actual maximum current with be subject to switching frequency, bus voltage and thermals.
Limited by time needed to 'refresh' high side bootstrap supply voltage.

Quick Start Procedure

Development board EPC9006 is easy to set up to evaluate the performance of the EPC2007 eGaN FET. Refer to Figure 2 for proper connect and measurement setup and follow the procedure below:

1. With power off, connect the input power supply bus to +VIN (J5,J6) and ground / return to –VIN (J7,J8).
2. With power off, connect the switch node of the half bridge OUT (J3,J4) to your circuit as required.
3. With power off, connect the gate drive input to +VDD (J1, Pin-1) and ground return to –VDD (J1, Pin-2).
4. With power off, connect the input PWM control signal to PWM (J2, Pin-1) and ground return to any of the remaining J2 pins.
5. Turn on the gate drive supply – make sure the supply is between 7 V and 12 V range.
6. Turn on the bus voltage to the required value (do not exceed the absolute maximum voltage of 100 V on VOUT).
7. Turn on the controller / PWM input source and probe switching node to see switching operation.
8. Once operational, adjust the bus voltage and load PWM control within the operating range and observe the output switching behavior, efficiency and other parameters.
9. For shutdown, please follow steps in reverse.

NOTE. When measuring the high frequency content switch node (OUT), care must be taken to avoid long ground leads. Measure the switch node (OUT) by placing the oscilloscope probe tip through the large via on the switch node (designed for this purpose) and grounding the probe directly across the GND terminals provided. See Figure 3 for proper scope probe technique. Do not let the probe tip touch the low-side die.

THERMAL CONSIDERATIONS

The EPC9006 development board showcases the EPC2007 eGaN FET. Although the electrical performance surpasses that for traditional Si devices, their relatively smaller size does magnify the thermal management requirements. The EPC9006 is intended for bench evaluation with low ambient temperature and convection cooling. The addition of heat-sinking and forced air cooling can significantly increase the current rating of these devices, but care must be taken to not exceed the absolute maximum die temperature of 125°C.

NOTE. The EPC9006 development board does not have any current or thermal protection on board.

Figure 1: Block Diagram of EPC9006 Development Board

Figure 4: Typical Waveforms for V_{IN} = 48 V to 5 V/5 A (1000kHz) Buck converter
CH1: V_{PWM} Input voltage – CH2: (I_{OUT}) Switch node current – CH4: (V_{OUT}) Switch node voltage

Figure 2: Proper Connection and Measurement Setup

Figure 3: Proper Measurement of Switch Node – OUT

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Development Board EPC9006 Quick Start Guide

100 V Half-Bridge with Gate Drive, Using EPC2007

EFFICIENT POWER CONVERSION

DESCRIPTION

The EPC9006 development board is a 100 V maximum device voltage, 5 A maximum output current, half bridge with onboard gate drives, featuring the EPC2007 enhancement mode (eGaN®) field effect transistor (FET). The purpose of this development board is to simplify the evaluation process of the EPC2007 eGaN FET by including all the critical components on a single board that can be easily connected into any existing converter.

The EPC9006 development board is 2" x 1.5" and contains not only two EPC2007 eGaN FET in a half bridge configuration using National LM5113 gate driver, supply and bypass capacitors. The board contains all critical components and layout for optimal switching performance. There are also various probe points to facilitate simple waveform measurement and efficiency calculation. A complete block diagram of the circuit is given in Figure 1.

For more information on the EPC2007s eGaN FET please refer to the datasheet available from EPC at www.epc-co.com. The datasheet should be read in conjunction with this quick start guide.

Table 1 Performance Summary (T_A = 25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNITS
V_{DD}	Gate Drive Input Supply Range		7	12	V
V_{IN}	Bus Input Voltage Range			70*	V
V_{OUT}	Switch Node Output Voltage			100	V
I_{OUT}	Switch Node Output Current			5*	A
V_{PWM}	PWM Logic Input Voltage Threshold	Input 'High'	3.5	6	V
		Input 'Low'	0	1.5	V
	Minimum 'High' State Input Pulse Width	V_{PWM} rise and fall time < 10ns	30		ns
	Minimum 'Low' State Input Pulse Width	V_{PWM} rise and fall time < 10ns	100#		ns

*Assumes inductive load, maximum current depends on die temperature – actual maximum current with be subject to switching frequency, bus voltage and thermals.
Limited by time needed to 'refresh' high side bootstrap supply voltage.

Quick Start Procedure

Development board EPC9006 is easy to set up to evaluate the performance of the EPC2007 eGaN FET. Refer to Figure 2 for proper connect and measurement setup and follow the procedure below:

1. With power off, connect the input power supply bus to +VIN (J5,J6) and ground / return to –VIN (J7,J8).
2. With power off, connect the switch node of the half bridge OUT (J3,J4) to your circuit as required.
3. With power off, connect the gate drive input to +VDD (J1, Pin-1) and ground return to –VDD (J1, Pin-2).
4. With power off, connect the input PWM control signal to PWM (J2, Pin-1) and ground return to any of the remaining J2 pins.
5. Turn on the gate drive supply – make sure the supply is between 7 V and 12 V range.
6. Turn on the bus voltage to the required value (do not exceed the absolute maximum voltage of 100 V on VOUT).
7. Turn on the controller / PWM input source and probe switching node to see switching operation.
8. Once operational, adjust the bus voltage and load PWM control within the operating range and observe the output switching behavior, efficiency and other parameters.
9. For shutdown, please follow steps in reverse.

NOTE. When measuring the high frequency content switch node (OUT), care must be taken to avoid long ground leads. Measure the switch node (OUT) by placing the oscilloscope probe tip through the large via on the switch node (designed for this purpose) and grounding the probe directly across the GND terminals provided. See Figure 3 for proper scope probe technique. Do not let the probe tip touch the low-side die.

THERMAL CONSIDERATIONS

The EPC9006 development board showcases the EPC2007 eGaN FET. Although the electrical performance surpasses that for traditional Si devices, their relatively smaller size does magnify the thermal management requirements. The EPC9006 is intended for bench evaluation with low ambient temperature and convection cooling. The addition of heat-sinking and forced air cooling can significantly increase the current rating of these devices, but care must be taken to not exceed the absolute maximum die temperature of 125°C.

NOTE. The EPC9006 development board does not have any current or thermal protection on board.

Figure 1: Block Diagram of EPC9006 Development Board

Figure 4: Typical Waveforms for V_{IN} = 48 V to 5 V/5 A (1000kHz) Buck converter
CH1: V_{PWM} Input voltage – CH2: (I_{OUT}) Switch node current – CH4: (V_{OUT}) Switch node voltage

Figure 2: Proper Connection and Measurement Setup

Figure 3: Proper Measurement of Switch Node – OUT

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EFFICIENT POWER CONVERSION

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Development Board EPC9006 Quick Start Guide

100 V Half-Bridge with Gate Drive, Using EPC2007

EFFICIENT POWER CONVERSION

DESCRIPTION

The EPC9006 development board is a 100 V maximum device voltage, 5 A maximum output current, half bridge with onboard gate drives, featuring the EPC2007 enhancement mode (eGaN®) field effect transistor (FET). The purpose of this development board is to simplify the evaluation process of the EPC2007 eGaN FET by including all the critical components on a single board that can be easily connected into any existing converter.

The EPC9006 development board is 2" x 1.5" and contains not only two EPC2007 eGaN FET in a half bridge configuration using National LM5113 gate driver, supply and bypass capacitors. The board contains all critical components and layout for optimal switching performance. There are also various probe points to facilitate simple waveform measurement and efficiency calculation. A complete block diagram of the circuit is given in Figure 1.

For more information on the EPC2007s eGaN FET please refer to the datasheet available from EPC at www.epc-co.com. The datasheet should be read in conjunction with this quick start guide.

Table 1 Performance Summary (T_A = 25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNITS
V_{DD}	Gate Drive Input Supply Range		7	12	V
V_{IN}	Bus Input Voltage Range			70*	V
V_{OUT}	Switch Node Output Voltage			100	V
I_{OUT}	Switch Node Output Current			5*	A
V_{PWM}	PWM Logic Input Voltage Threshold	Input 'High'	3.5	6	V
		Input 'Low'	0	1.5	V
	Minimum 'High' State Input Pulse Width	V_{PWM} rise and fall time < 10ns	30		ns
	Minimum 'Low' State Input Pulse Width	V_{PWM} rise and fall time < 10ns	100#		ns

*Assumes inductive load, maximum current depends on die temperature – actual maximum current with be subject to switching frequency, bus voltage and thermals.
Limited by time needed to 'refresh' high side bootstrap supply voltage.

Quick Start Procedure

Development board EPC9006 is easy to set up to evaluate the performance of the EPC2007 eGaN FET. Refer to Figure 2 for proper connect and measurement setup and follow the procedure below:

1. With power off, connect the input power supply bus to +VIN (J5,J6) and ground / return to –VIN (J7,J8).
2. With power off, connect the switch node of the half bridge OUT (J3,J4) to your circuit as required.
3. With power off, connect the gate drive input to +VDD (J1, Pin-1) and ground return to –VDD (J1, Pin-2).
4. With power off, connect the input PWM control signal to PWM (J2, Pin-1) and ground return to any of the remaining J2 pins.
5. Turn on the gate drive supply – make sure the supply is between 7 V and 12 V range.
6. Turn on the bus voltage to the required value (do not exceed the absolute maximum voltage of 100 V on VOUT).
7. Turn on the controller / PWM input source and probe switching node to see switching operation.
8. Once operational, adjust the bus voltage and load PWM control within the operating range and observe the output switching behavior, efficiency and other parameters.
9. For shutdown, please follow steps in reverse.

NOTE. When measuring the high frequency content switch node (OUT), care must be taken to avoid long ground leads. Measure the switch node (OUT) by placing the oscilloscope probe tip through the large via on the switch node (designed for this purpose) and grounding the probe directly across the GND terminals provided. See Figure 3 for proper scope probe technique. Do not let the probe tip touch the low-side die.

THERMAL CONSIDERATIONS

The EPC9006 development board showcases the EPC2007 eGaN FET. Although the electrical performance surpasses that for traditional Si devices, their relatively smaller size does magnify the thermal management requirements. The EPC9006 is intended for bench evaluation with low ambient temperature and convection cooling. The addition of heat-sinking and forced air cooling can significantly increase the current rating of these devices, but care must be taken to not exceed the absolute maximum die temperature of 125°C.

NOTE. The EPC9006 development board does not have any current or thermal protection on board.

Figure 1: Block Diagram of EPC9006 Development Board

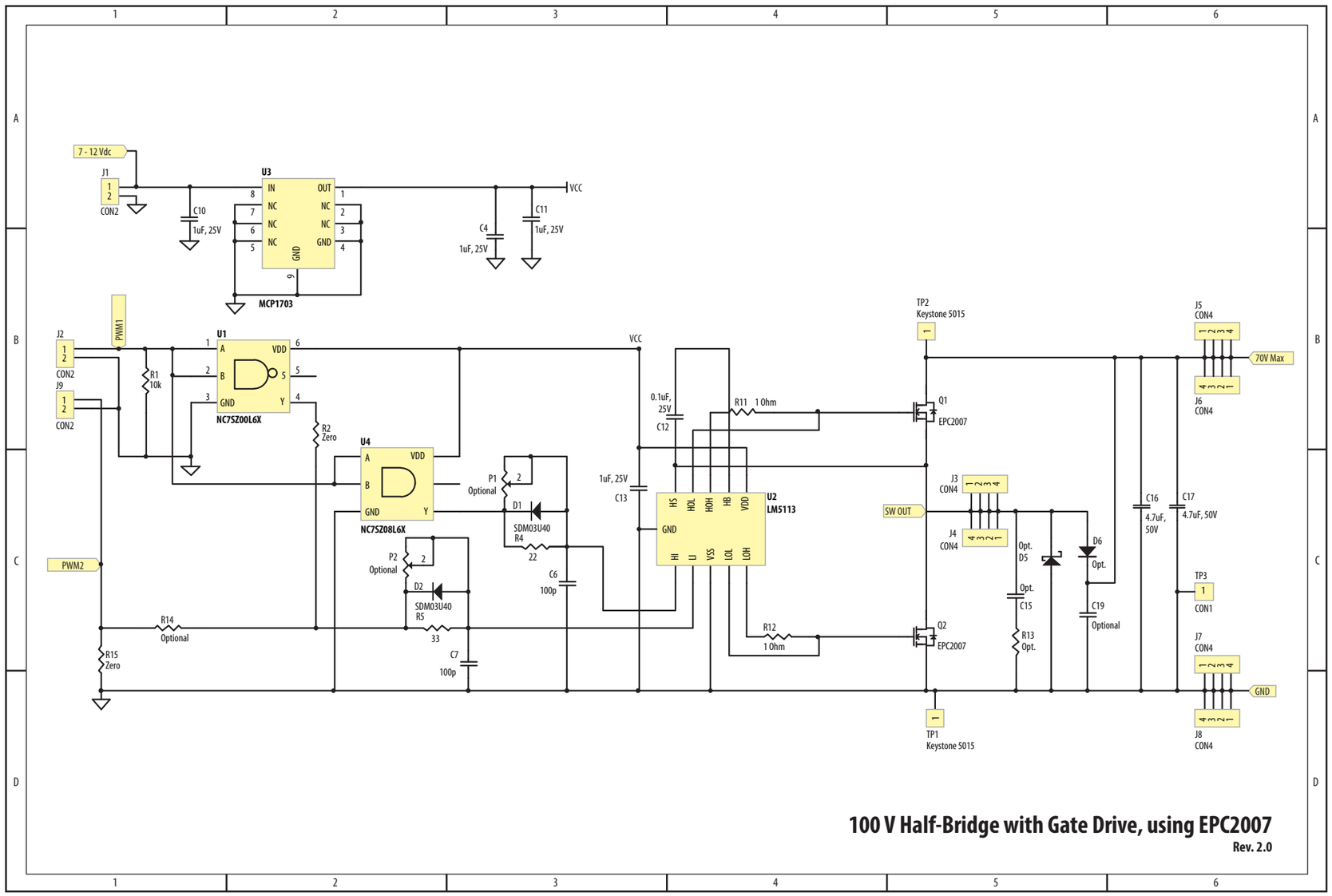
Figure 4: Typical Waveforms for V_{IN} = 48 V to 5 V/5 A (1000kHz) Buck converter
CH1: V_{PWM} Input voltage – CH2: (I_{OUT}) Switch node current – CH4: (V_{OUT}) Switch node voltage

Figure 2: Proper Connection and Measurement Setup

Figure 3: Proper Measurement of Switch Node – OUT

16	1	U1	I.C., Logic	Fairchild, NC7SZ00L6X
17	1	U2	I.C., Gate driver	Texas Instruments, LM5113
18	1	U3	I.C., Regulator	Microchip, MCP1703T-5002E/MC
19	1	U4	I.C., Logic	Fairchild, NC7SZ08L6X
20	0	R13, R14	Optional Resistor	
21	0	C15, C19	Optional Capacitor	
22	0	D5, D6	Optional Diode	
23	0	P1, P2	Optional Potentiometer	

Note 1: 36 pin Header to be cut as follows:
J1: cut 2 pins used
J2 & J9: cut 4 pins used
TP3: cut 1 pin used



16	1	U1	I.C., Logic	Fairchild, NC7SZ00L6X
17	1	U2	I.C., Gate driver	Texas Instruments, LM5113
18	1	U3	I.C., Regulator	Microchip, MCP1703T-5002E/MC
19	1	U4	I.C., Logic	Fairchild, NC7SZ08L6X
20	0	R13, R14	Optional Resistor	
21	0	C15, C19	Optional Capacitor	
22	0	D5, D6	Optional Diode	
23	0	P1, P2	Optional Potentiometer	

Note 1: 36 pin Header to be cut as follows:
J1: cut 2 pins used
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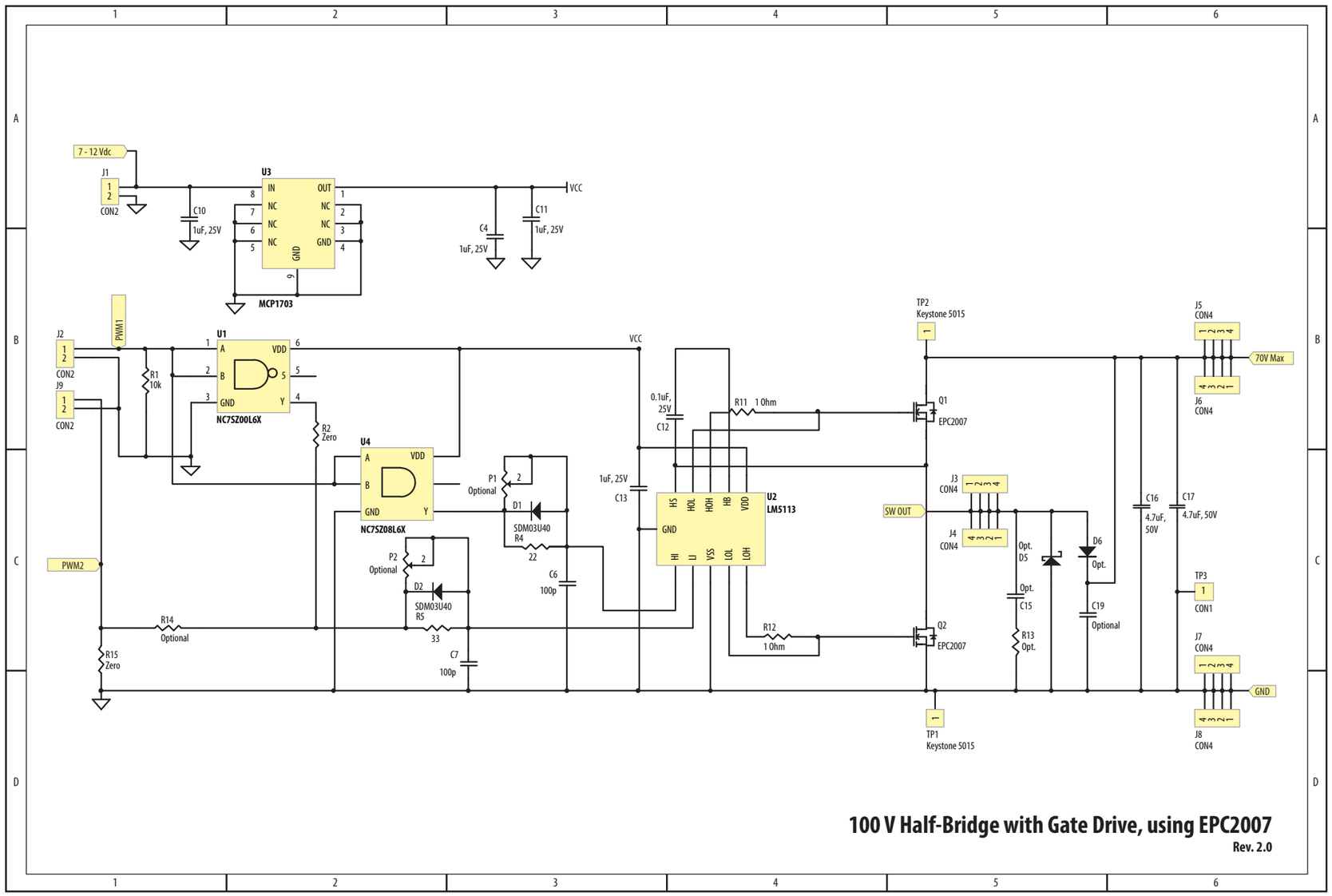
TP3: cut 1 pin used



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Development Board EPC9006 Quick Start Guide

100 V Half-Bridge with Gate Drive, Using EPC2007

EFFICIENT POWER CONVERSION

DESCRIPTION

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The EPC9006 development board is 2" x 1.5" and contains not only two EPC2007 eGaN FET in a half bridge configuration using National LM5113 gate driver, supply and bypass capacitors. The board contains all critical components and layout for optimal switching performance. There are also various probe points to facilitate simple waveform measurement and efficiency calculation. A complete block diagram of the circuit is given in Figure 1.

For more information on the EPC2007s eGaN FET please refer to the datasheet available from EPC at www.epc-co.com. The datasheet should be read in conjunction with this quick start guide.

Table 1 Performance Summary (T_A = 25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNITS
V_{DD}	Gate Drive Input Supply Range		7	12	V
V_{IN}	Bus Input Voltage Range			70*	V
V_{OUT}	Switch Node Output Voltage			100	V
I_{OUT}	Switch Node Output Current			5*	A
V_{PWM}	PWM Logic Input Voltage Threshold	Input 'High'	3.5	6	V
		Input 'Low'	0	1.5	V
	Minimum 'High' State Input Pulse Width	V_{PWM} rise and fall time < 10ns	30		ns
	Minimum 'Low' State Input Pulse Width	V_{PWM} rise and fall time < 10ns	100#		ns

*Assumes inductive load, maximum current depends on die temperature – actual maximum current with be subject to switching frequency, bus voltage and thermals.
Limited by time needed to 'refresh' high side bootstrap supply voltage.

Quick Start Procedure

Development board EPC9006 is easy to set up to evaluate the performance of the EPC2007 eGaN FET. Refer to Figure 2 for proper connect and measurement setup and follow the procedure below:

1. With power off, connect the input power supply bus to +VIN (J5,J6) and ground / return to –VIN (J7,J8).
2. With power off, connect the switch node of the half bridge OUT (J3,J4) to your circuit as required.
3. With power off, connect the gate drive input to +VDD (J1, Pin-1) and ground return to –VDD (J1, Pin-2).
4. With power off, connect the input PWM control signal to PWM (J2, Pin-1) and ground return to any of the remaining J2 pins.
5. Turn on the gate drive supply – make sure the supply is between 7 V and 12 V range.
6. Turn on the bus voltage to the required value (do not exceed the absolute maximum voltage of 100 V on VOUT).
7. Turn on the controller / PWM input source and probe switching node to see switching operation.
8. Once operational, adjust the bus voltage and load PWM control within the operating range and observe the output switching behavior, efficiency and other parameters.
9. For shutdown, please follow steps in reverse.

NOTE. When measuring the high frequency content switch node (OUT), care must be taken to avoid long ground leads. Measure the switch node (OUT) by placing the oscilloscope probe tip through the large via on the switch node (designed for this purpose) and grounding the probe directly across the GND terminals provided. See Figure 3 for proper scope probe technique. Do not let the probe tip touch the low-side die.

THERMAL CONSIDERATIONS

The EPC9006 development board showcases the EPC2007 eGaN FET. Although the electrical performance surpasses that for traditional Si devices, their relatively smaller size does magnify the thermal management requirements. The EPC9006 is intended for bench evaluation with low ambient temperature and convection cooling. The addition of heat-sinking and forced air cooling can significantly increase the current rating of these devices, but care must be taken to not exceed the absolute maximum die temperature of 125°C.

NOTE. The EPC9006 development board does not have any current or thermal protection on board.

Figure 1: Block Diagram of EPC9006 Development Board

Figure 4: Typical Waveforms for V_{IN} = 48 V to 5 V/5 A (1000kHz) Buck converter
CH1: V_{PWM} Input voltage – CH2: (I_{OUT}) Switch node current – CH4: (V_{OUT}) Switch node voltage

Figure 2: Proper Connection and Measurement Setup

Figure 3: Proper Measurement of Switch Node – OUT

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